FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. DLED.004CP1C1	APPLICATION NO. 10/689,544
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	APPLICANT Vasily I. Shveykin	
(USE SEVERAL SHEETS IF NECESSARY)	FILING DATE October 20, 2003	GROUP ~~2812~~ 2826

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
MLT	1	4,063,189	12/13/77	Scifres et al.			
	2	5,101,413	3/31/92	Botez			
	3	5,537,433	7/16/96	Watanabe			
	4	5,705,834	1/1998	Egalon et al.			
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	6	5,793,062	8/1998	Kish, Jr. et al.			
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MLT	10	6,649,938	11/2003	Bogatov et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
MLT	11	SU 1329533 A1	05/1998	Soviet Union			X	
	12	SU 1359833 A1	15/12/87	Soviet Union			X	
	13	1,455,373	30/01/89	Soviet Union				
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	15	2,134,007	07/27/99	Russia			X	
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	23	WO 99/46838	09/1999	WIPO			X	
MLT	24	WO 99/08352	02/1999	WIPO				

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MLT	25	WO 00/10235	02/2000	WIPO			X	
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